

Form PTO-1449 Department of Commerce Patent and Trademark Office INFORMATION DISCLOSURE STATEMENT IN AN APPLICATION (Use several sheets if necessary)	Docket No. PAT004	Serial No. Unassigned
	Applicants Wen-Yen Hwang	
	Filing Date Herewith	Group Art Unit Unassigned

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
JN	5,285,086	02/08/94	Fitzgerald, Jr.			
	5,294,808	03/15/94	Lo			
	5,513,204	04/30/96	Jayaraman			
	5,719,894	02/17/98	Jewell <i>et al.</i>			
	5,754,578	5/19/98	Jayaraman			
	5,914,976	6/22/99	Jayaraman <i>et al.</i>			
	5,981,400	11/09/99	Lo			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO	

OTHER (Including Author, Title, Date, Pertinent Pages, Etc.)

JN	Matthews, J. W. and Blakeslee, A. E., "Defects in Epitaxial Multilayers," <i>Journal of Crystal Growth</i> 27, (1974), pp. 118-125.
	Parillaud <i>et al.</i> , "High Quality InP on Si by Conformal Growth," <i>Appl. Phys. Lett.</i> 68, (1996), p. 2654.
	Lo, Yu-Hwa, "Long Wavelength Vertical Cavity Surface Emitting Lasers," <i>Hot Topic</i> , February 1995, p. 20-21.

EXAMINER	JOSEPH NGUYEN	DATE CONSIDERED	10/11/02
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

1c971 U.S. PTO
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JN	Qian <i>et al.</i> , "1.3 μ m Vertical-Cavity Surface-Emitting Lasers with Double-Bonded GaAs-AlAs Bragg Mirrors," <i>IEEE Photonics Technology Letters</i> , Vol. 9, No. 1, January 1997, pp. 8-10. ✓
	Uchiyam <i>et al.</i> , "Continuous-Wave Operation up to 36°C of 1.3 μ m GaInAsP-InP Vertical-Cavity Surface-Emitting Lasers," <i>IEEE Photonics Technology Letters</i> , Vol. 9, No. 2, February 1997, pp. 141-142. ✓
	Dudley, <i>et al.</i> , "Low Threshold, Wafer Fused Long Wavelength Vertical Cavity Lasers," <i>Appl. Phys. Lett.</i> 64 (12), March 1994, pp. 1463-1465. ✓
	Xiong, Yanyan and Lo, Yu-Hwa, "Current Spreading and Carrier Diffusion in Long-Wavelength Vertical-Cavity Surface-Emitting Lasers," <i>IEEE Photonics Technology Letters</i> , Vol. 10, No. 9, September 1998, pp. 1202-1204. ✓
	Salet <i>et al.</i> , "Undercut Ridge Structures: A Novel Approach to 1.3/1.55 μ m Vertical-Cavity Lasers Designed for Continuous-Wave Operation," <i>IEEE Proc.-Optoelectron.</i> , Vol. 145, No. 2, April 1998, pp. 125-131. ✓
	Salet <i>et al.</i> , "Room-Temperature Pulsed Operation of 1.3 μ m Vertical-Cavity Lasers Including Bottom InGaAsP/InP Multilayer Bragg Mirrors," <i>Electronics Letters</i> , Vol. 33, No. 24, November 1997, pp. 2048-2049. ✓

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IN	Salet <i>et al.</i> , "Gas-Source Molecular-Beam Epitaxy and Optical Characterisation of Highly-Reflective InGaAsP/InP Multilayer Bragg Mirrors for 1.3µm Vertical-Cavity Lasers," <i>Electronics Letters</i> , Vol. 33, No. 13, June 1997, pp. 1145-1147. ✓					
I	Qian, <i>et al.</i> , "Submilliamp 1.3µm Vertical-Cavity Surface-Emitting Lasers With Threshold Current Density of <500A/cm²," <i>Electronics Letters</i> , Vol. 33, No. 12, June 1997, pp. 1052-1054. ✓					
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